



Features

- High blocking voltage with low On-resistance
- High speed switching with low capacitances
- Fast intrinsic diode with low reverse recovery (Qrr)
- Halogen free, RoHS compliant

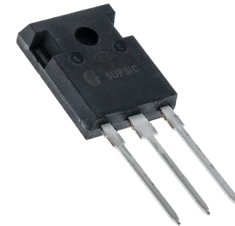
Benefits

- Higher system efficiency
- Reduced cooling requirements
- Increased power density
- Increased system switching frequency

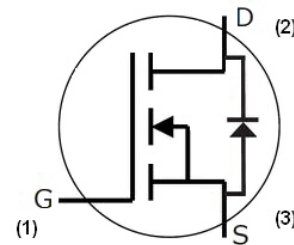
Applications

- Renewable energy
- EV battery chargers
- High voltage DC/DC converters
- Switch Mode Power Supplies

V_{DS}	900 V
$I_D @ 25^\circ\text{C}$	36 A
$R_{DS(on)}$	65 m Ω



TO-247-3
Package



Part Number	Package	Marking
GC3M0065090D	TO-247-3	GC3M0065090

Maximum Ratings ($T_C = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Value	Unit	Test Conditions	Note
V_{DSmax}	Drain - Source Voltage	900	V	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	
V_{GSmax}	Gate - Source Voltage (dynamic)	-8/+19	V	AC ($f > 1\text{ Hz}$)	Note: 1
V_{GSop}	Gate - Source Voltage (static)	-4/+15	V	Static	Note: 2
I_D	Continuous Drain Current	36	A	$V_{GS} = 15\text{ V}, T_C = 25^\circ\text{C}$	Fig. 19
		23		$V_{GS} = 15\text{ V}, T_C = 100^\circ\text{C}$	
$I_{D(pulse)}$	Pulsed Drain Current	90	A	Pulse width t_p limited by T_{jmax}	Fig. 22
E_{AS}	Avalanche energy, Single pulse	110	mJ	$I_D = 22\text{ A}, V_{DD} = 50\text{ V}$	
P_D	Power Dissipation	125	W	$T_C = 25^\circ\text{C}, T_J = 150^\circ\text{C}$	Fig. 20
T_J, T_{stg}	Operating Junction and Storage Temperature	-55 to +150	$^\circ\text{C}$		
T_L	Solder Temperature	260	$^\circ\text{C}$	1.6mm (0.063") from case for 10s	
M_d	Mounting Torque	1	Nm lbf-in	M3 or 6-32 screw	
		8.8			

Note (1): When using MOSFET Body Diode $V_{GSmax} = -4\text{V}/+19\text{V}$

Note (2): MOSFET can also safely operate at 0/+15 V

Electrical Characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Min.	Typ.	Max.	Unit	Test Conditions	Note
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	900			V	$V_{GS} = 0\text{ V}, I_D = 100\ \mu\text{A}$	
$V_{GS(th)}$	Gate Threshold Voltage	1.8	2.1	3.5	V	$V_{DS} = V_{GS}, I_D = 5\ \text{mA}$	Fig. 11
			1.6		V	$V_{DS} = V_{GS}, I_D = 5\ \text{mA}, T_J = 150^\circ\text{C}$	
I_{DSS}	Zero Gate Voltage Drain Current		1	100	μA	$V_{DS} = 900\ \text{V}, V_{GS} = 0\ \text{V}$	
I_{GSS}	Gate-Source Leakage Current		10	250	nA	$V_{GS} = 15\ \text{V}, V_{DS} = 0\ \text{V}$	
$R_{DS(on)}$	Drain-Source On-State Resistance		65	78	m Ω	$V_{GS} = 15\ \text{V}, I_D = 20\ \text{A}$	Fig. 4, 5, 6
			90			$V_{GS} = 15\ \text{V}, I_D = 20\ \text{A}, T_J = 150^\circ\text{C}$	
g_{fs}	Transconductance		16		S	$V_{DS} = 20\ \text{V}, I_{DS} = 20\ \text{A}$	Fig. 7
			13			$V_{DS} = 20\ \text{V}, I_{DS} = 20\ \text{A}, T_J = 150^\circ\text{C}$	
C_{iss}	Input Capacitance		760		pF	$V_{GS} = 0\ \text{V}, V_{DS} = 600\ \text{V}$ $f = 1\ \text{MHz}$ $V_{AC} = 25\ \text{mV}$	Fig. 17, 18
C_{oss}	Output Capacitance		66				
C_{rss}	Reverse Transfer Capacitance		5.0				
E_{oss}	C_{oss} Stored Energy		16				μJ
E_{ON}	Turn-On Switching Energy (Body Diode FWD)		343		μJ	$V_{DS} = 400\ \text{V}, V_{GS} = -4\ \text{V}/15\ \text{V}, I_D = 20\ \text{A},$ $R_{G(ext)} = 2.5\ \Omega, L = 65.7\ \mu\text{H}, T_J = 150^\circ\text{C}$	Fig. 26, Note 3
E_{OFF}	Turn Off Switching Energy (Body Diode FWD)		46				
$t_{d(on)}$	Turn-On Delay Time		45		ns	$V_{DD} = 400\ \text{V}, V_{GS} = -4\ \text{V}/15\ \text{V}$ $I_D = 20\ \text{A}, R_{G(ext)} = 2.5\ \Omega,$ Timing relative to V_{DS} Inductive load	Fig. 27
t_r	Rise Time		13				
$t_{d(off)}$	Turn-Off Delay Time		20				
t_f	Fall Time		8				
$R_{G(int)}$	Internal Gate Resistance		3.5		Ω	$f = 1\ \text{MHz}, V_{AC} = 25\ \text{mV}$	
Q_{gs}	Gate to Source Charge		9		nC	$V_{DS} = 400\ \text{V}, V_{GS} = -4\ \text{V}/15\ \text{V}$ $I_D = 20\ \text{A}$ Per IEC60747-8-4 pg 21	Fig. 12
Q_{gd}	Gate to Drain Charge		13				
Q_g	Total Gate Charge		35				

Reverse Diode Characteristics ($T_c = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Typ.	Max.	Unit	Test Conditions	Note
V_{SD}	Diode Forward Voltage	4.4		V	$V_{GS} = -4\ \text{V}, I_{SD} = 10\ \text{A}$	Fig. 8, 9, 10
		4.0		V	$V_{GS} = -4\ \text{V}, I_{SD} = 10\ \text{A}, T_J = 150^\circ\text{C}$	
I_S	Continuous Diode Forward Current		23.5	A	$V_{GS} = -4\ \text{V}$	Note 1
$I_{S,pulse}$	Diode pulse Current		90	A	$V_{GS} = -4\ \text{V},$ pulse width t_p limited by T_{jmax}	Note 1
t_{rr}	Reverse Recovery time	26		ns	$V_{GS} = -4\ \text{V}, I_{SD} = 20\ \text{A}, V_R = 400\ \text{V}$ $dif/dt = 900\ \text{A}/\mu\text{s}, T_J = 150^\circ\text{C}$	Note 1
Q_{rr}	Reverse Recovery Charge	145		nC		
I_{rrm}	Peak Reverse Recovery Current	8		A		

Thermal Characteristics

Symbol	Parameter	Max.	Unit	Test Conditions	Note
$R_{\theta JC}$	Thermal Resistance from Junction to Case	1.0	$^\circ\text{C}/\text{W}$		Fig. 21
$R_{\theta JA}$	Thermal Resistance From Junction to Ambient	40			

Note (3): Turn-off and Turn-on switching energy and timing values measured using SiC MOSFET Body Diode

Typical Performance

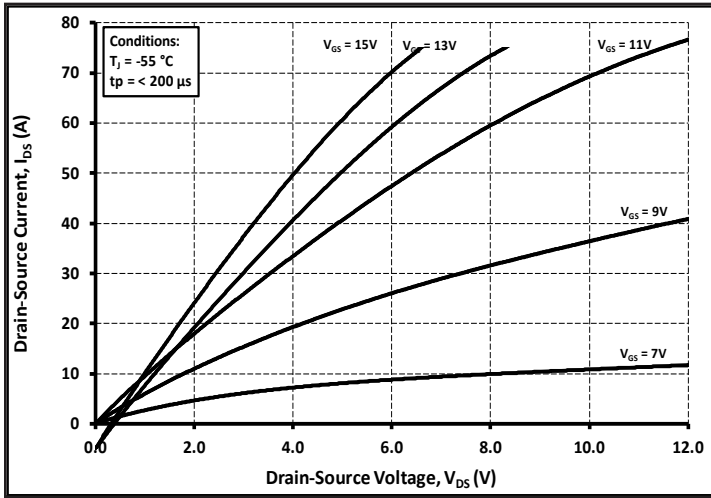


Figure 1. Output Characteristics $T_J = -55\text{ }^\circ\text{C}$

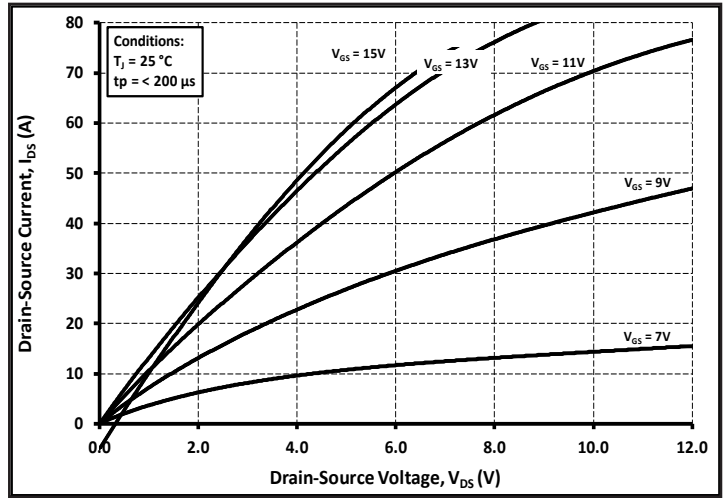


Figure 2. Output Characteristics $T_J = 25\text{ }^\circ\text{C}$

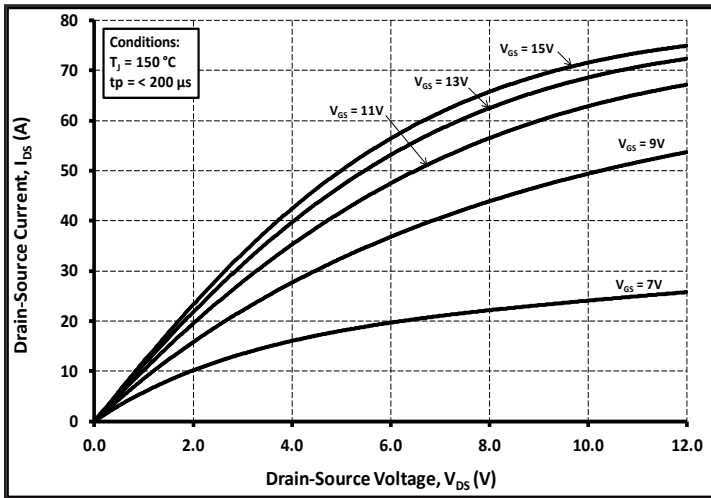


Figure 3. Output Characteristics $T_J = 150\text{ }^\circ\text{C}$

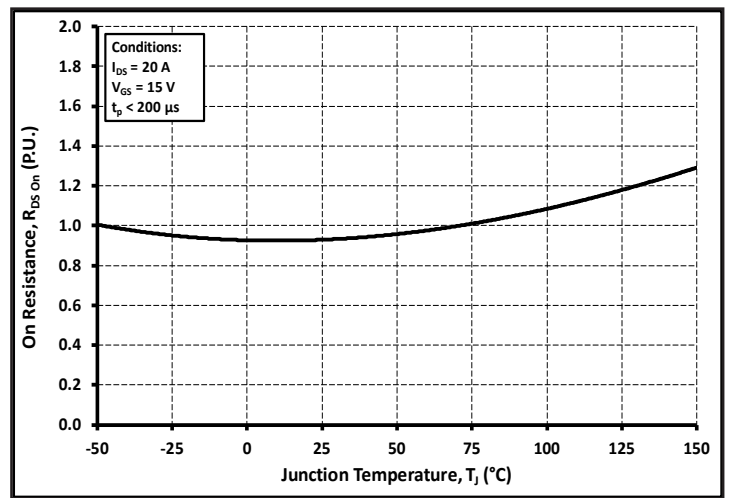


Figure 4. Normalized On-Resistance vs. Temperature

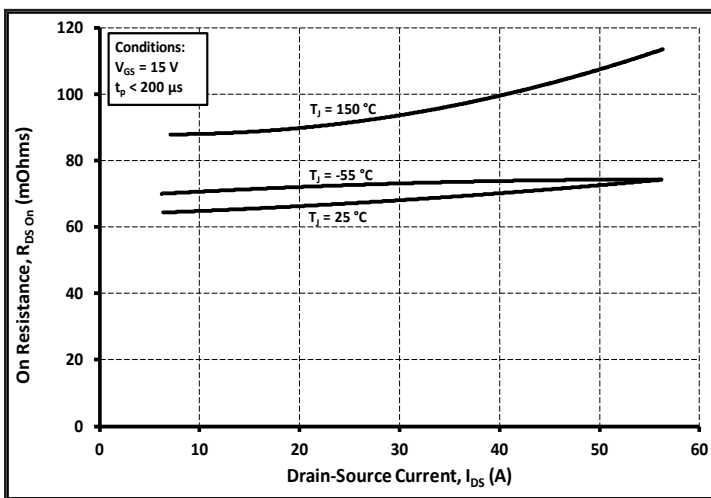


Figure 5. On-Resistance vs. Drain Current For Various Temperatures

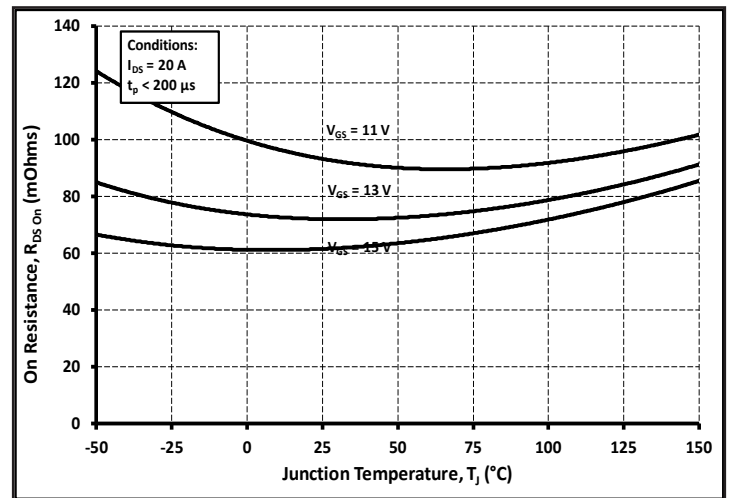


Figure 6. On-Resistance vs. Temperature For Various Gate Voltage

Typical Performance

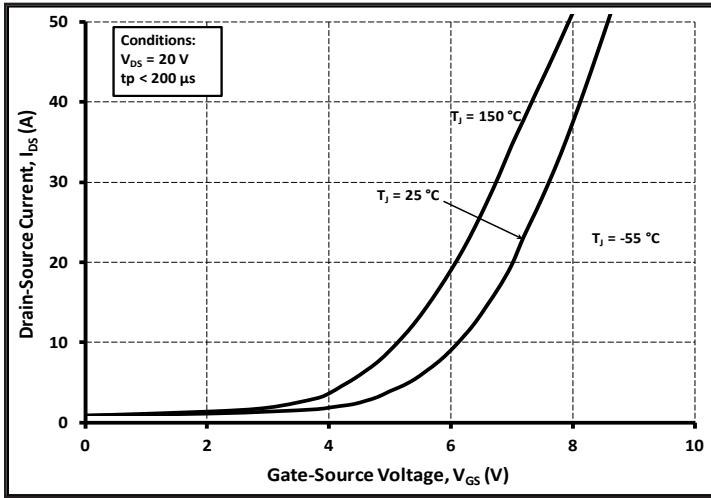


Figure 7. Transfer Characteristic for Various Junction Temperatures

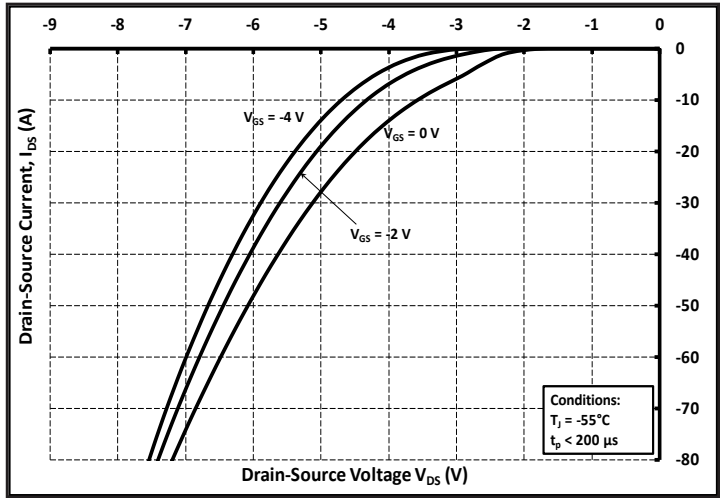


Figure 8. Body Diode Characteristic at -55 °C

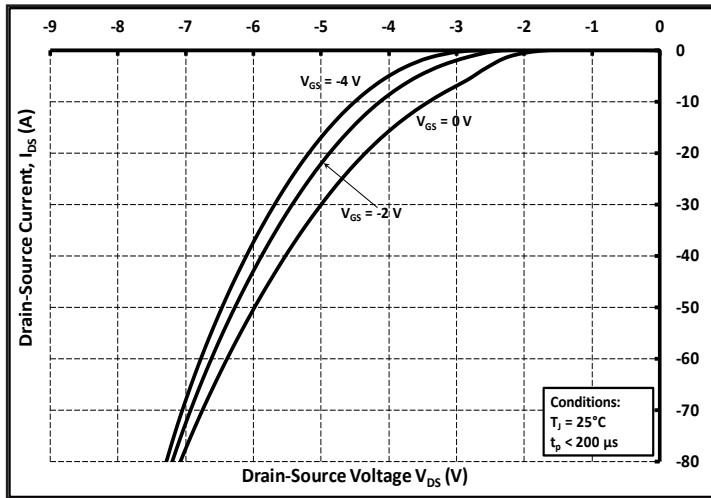


Figure 9. Body Diode Characteristic at 25 °C

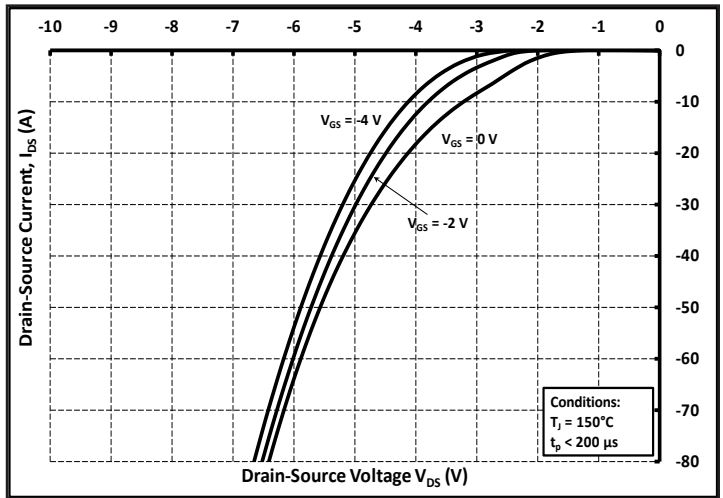


Figure 10. Body Diode Characteristic at 150 °C

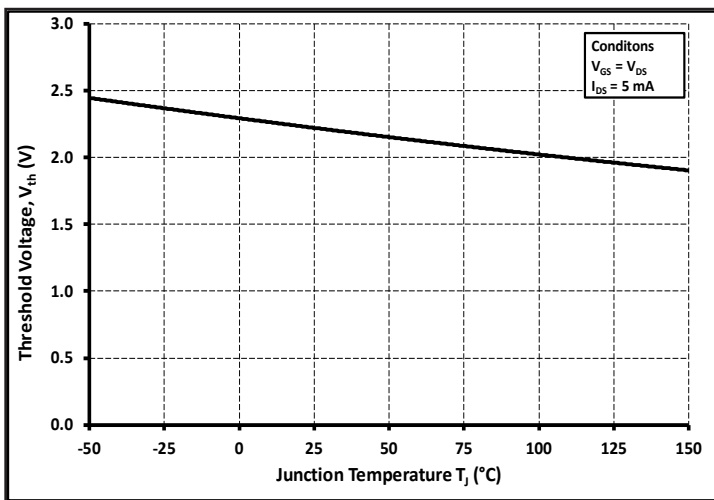


Figure 11. Threshold Voltage vs. Temperature

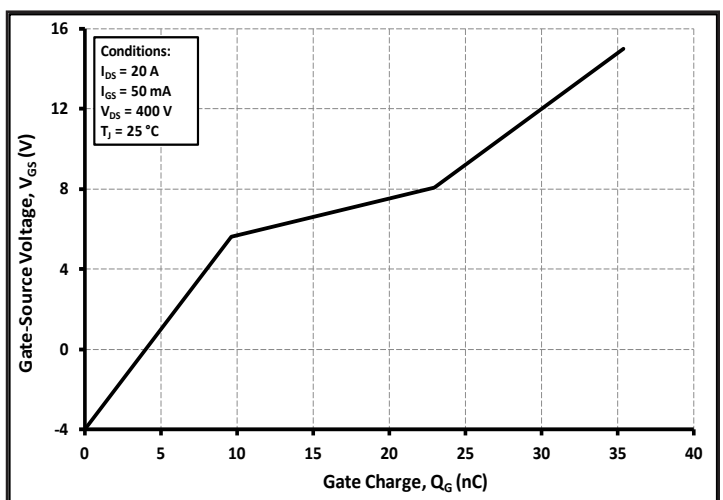


Figure 12. Gate Charge Characteristics

Typical Performance

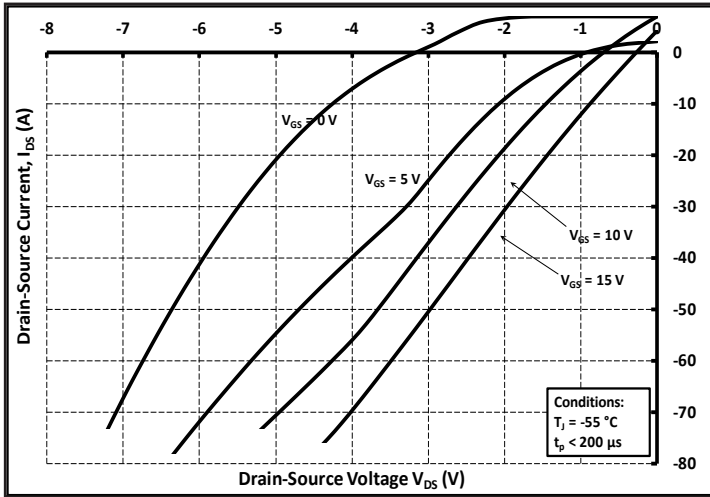


Figure 13. 3rd Quadrant Characteristic at -55 °C

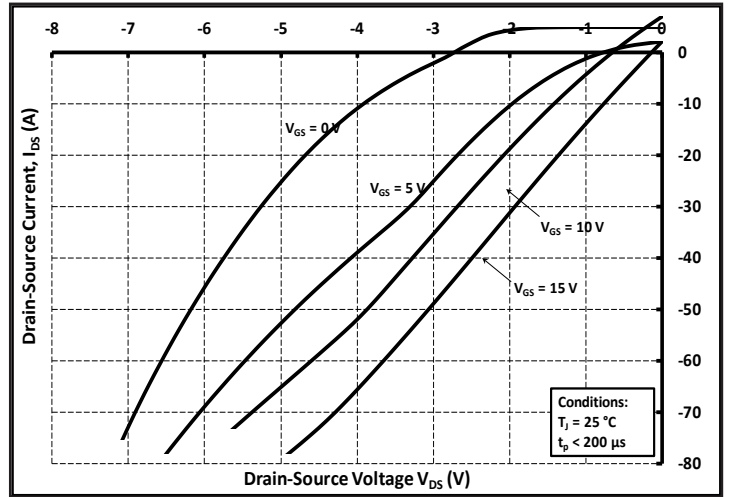


Figure 14. 3rd Quadrant Characteristic at 25 °C

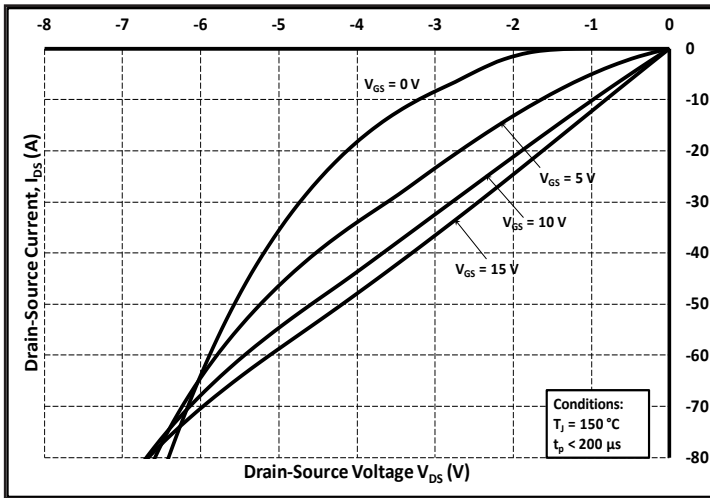


Figure 15. 3rd Quadrant Characteristic at 150 °C

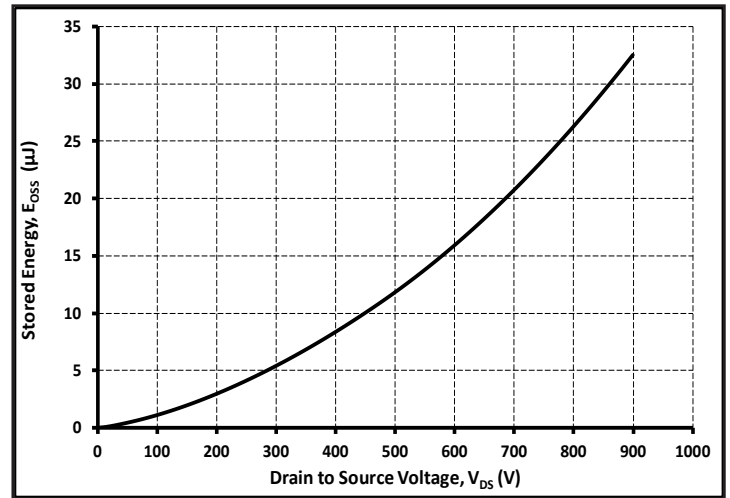


Figure 16. Output Capacitor Stored Energy

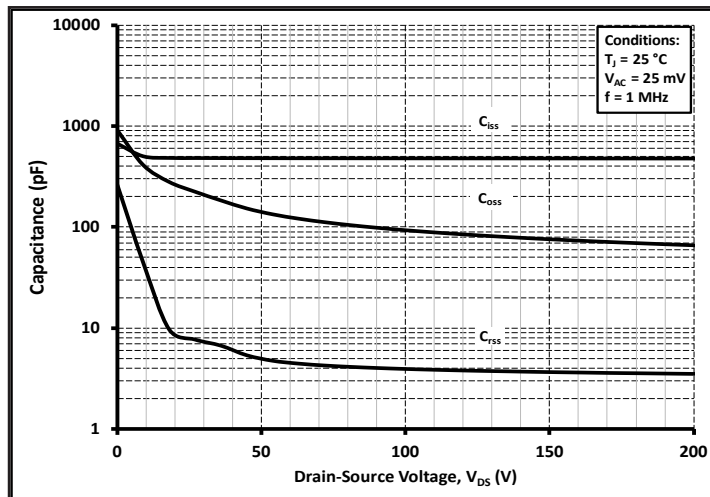


Figure 17. Capacitances vs. Drain-Source Voltage (0 - 200V)

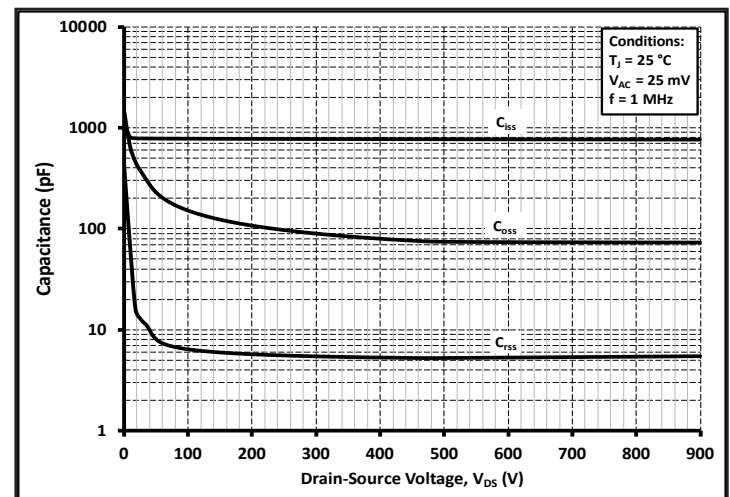


Figure 18. Capacitances vs. Drain-Source Voltage (0 - 900V)

Typical Performance

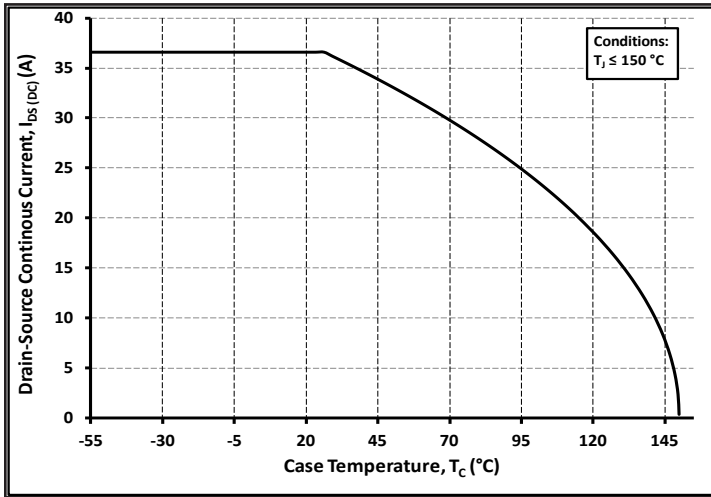


Figure 19. Continuous Drain Current Derating vs. Case Temperature

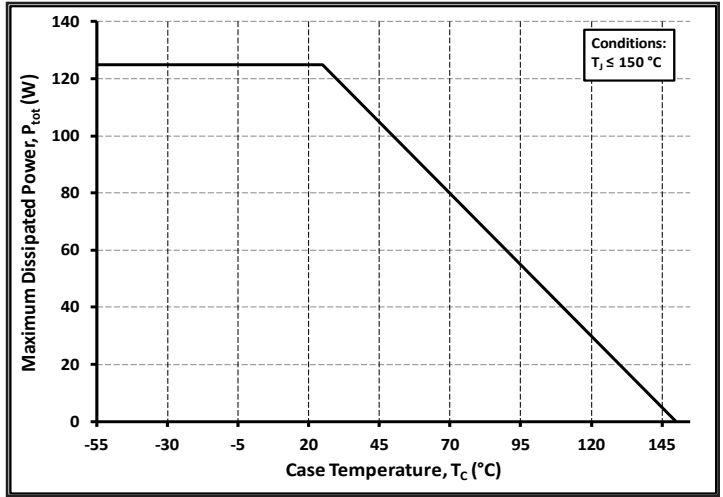


Figure 20. Maximum Power Dissipation Derating vs. Case Temperature

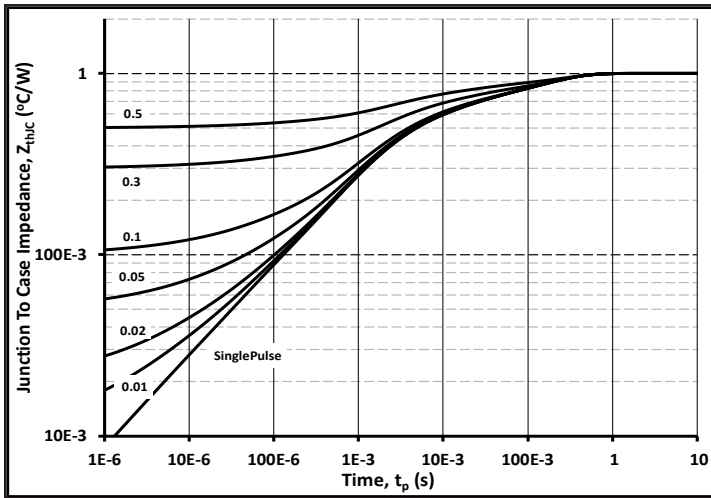


Figure 21. Transient Thermal Impedance (Junction - Case)

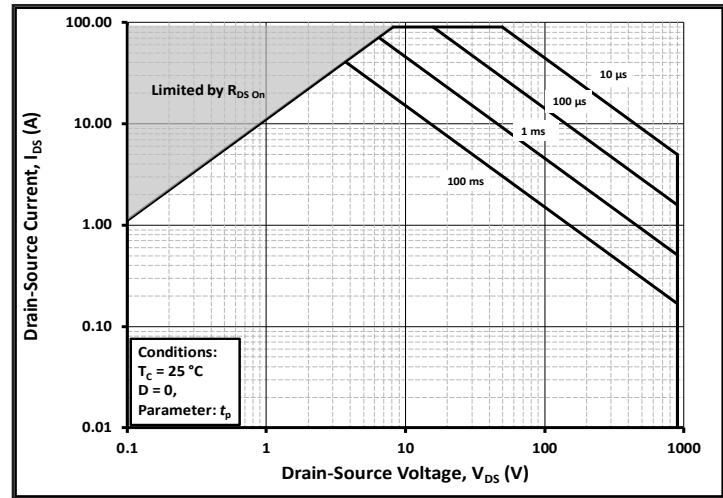


Figure 22. Safe Operating Area

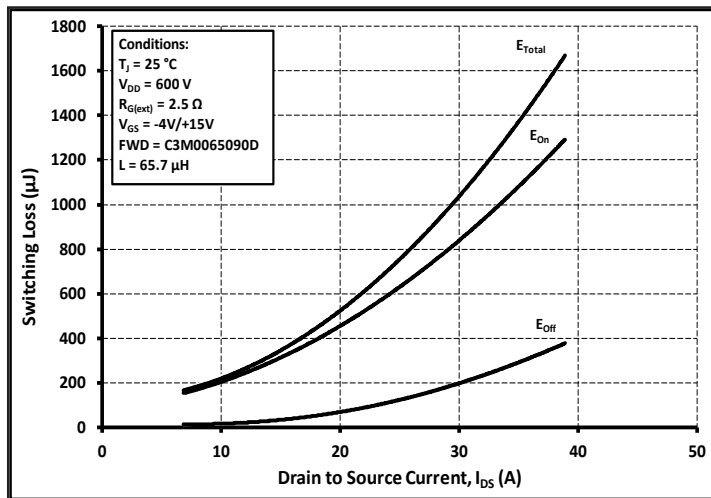


Figure 23. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 600V$)

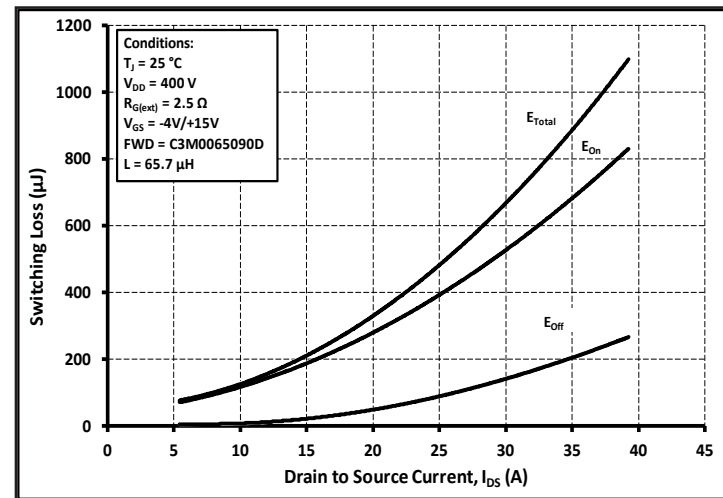


Figure 24. Clamped Inductive Switching Energy vs. Drain Current ($V_{DD} = 400V$)

Typical Performance

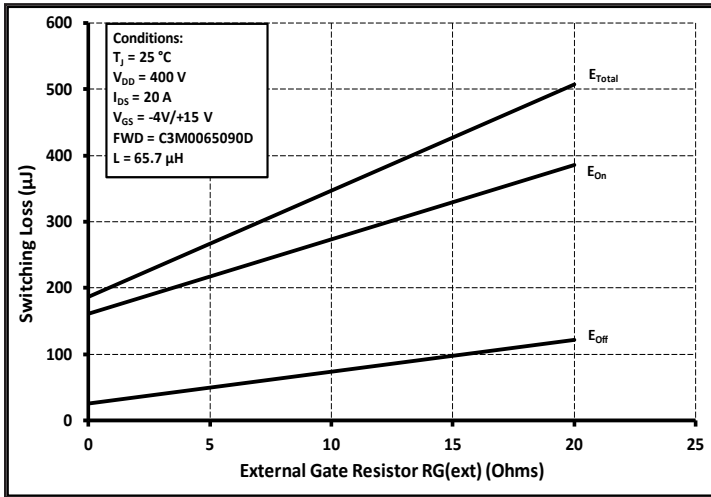


Figure 25. Clamped Inductive Switching Energy vs. $R_{G(ext)}$

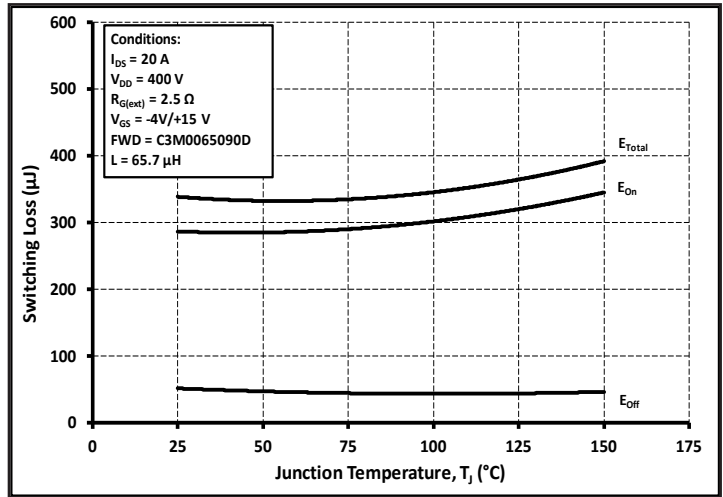


Figure 26. Clamped Inductive Switching Energy vs. Temperature

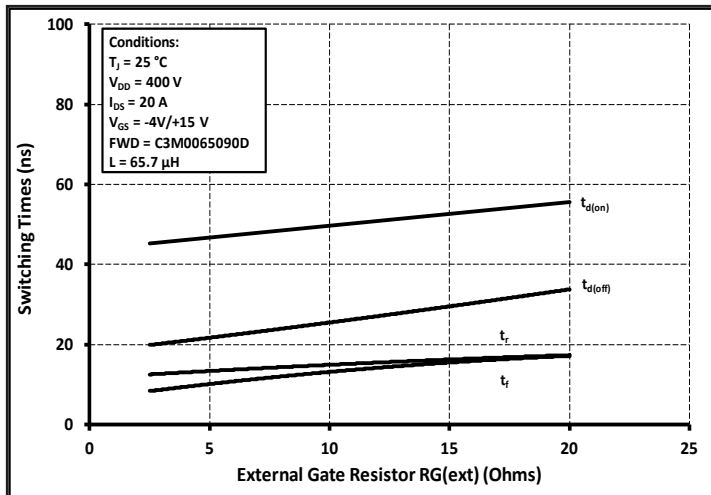


Figure 27. Switching Times vs. $R_{G(ext)}$

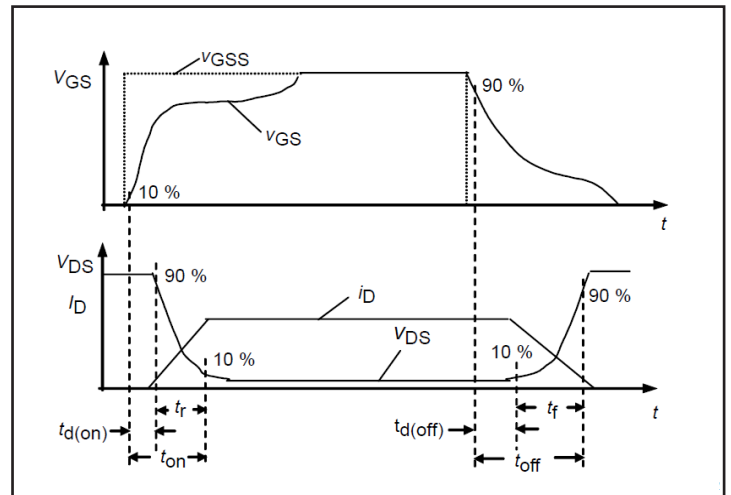


Figure 28. Switching Times Definition

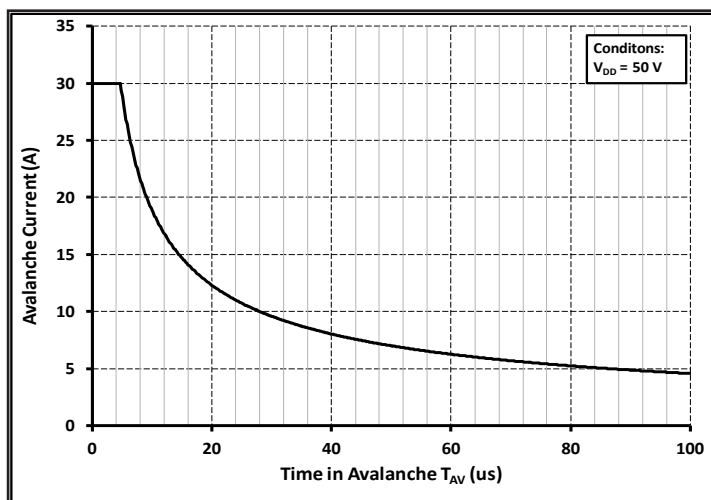


Figure 29. Single Avalanche SOA curve

Test Circuit Schematic

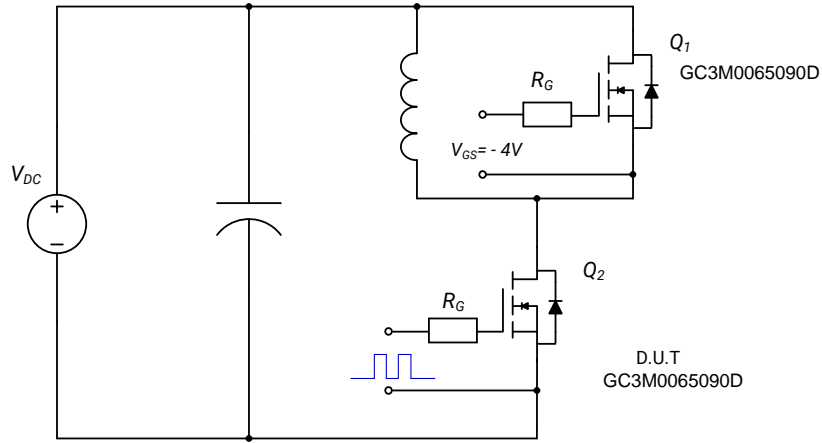


Figure 30. Clamped Inductive Switching
Waveform Test Circuit

Note (3): Turn-off and Turn-on switching energy and timing values measured using SiC MOSFET Body Diode as shown above.

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